

**Amendment to the Specification**

At page 6, lines 1-3, please delete the following paragraph, as shown:

~~FIG. 5 shows two modes of operation of an insulated gate device, with each mode corresponding, for example, to current flow as shown in FIGs. 3 and 4, respectively, according to another example embodiment of the present invention;~~

At page 18, lines 3-15, please amend the following paragraph, as shown:

~~FIG. 5 shows overall~~ Overall device characteristics of a semiconductor device that may, for example, be implemented in connection with the approaches discussed in connection with FIGs. 3 and 4 above. For purposes of discussion, “Mode 1” breakdown refers to breakdown occurring in connection with FIG. 3, and “Mode 2” breakdown refers to breakdown occurring in connection with FIG. 4, with a germanium-based substrate, such as that shown in FIG. 1A, at a temperature of about 400K. With this approach, the subthreshold slope for both Mode 1 and Mode 2 is about 5 mV/decade (positive or negative, respectively), which is much lower than  $kT/q$ . In one implementation, the characteristics ~~shown~~ are shifted about the  $V_G$  axis by tuning the gate workfunction. The gate workfunction can be tuned (*i.e.*, set), for example, by doping the gate to set the bias presented to an intermediate region in response to a particular voltage applied to the gate and/or changing a dielectric material or thickness of dielectric between the gate and the intermediate region.